## NSN 5961-01-627-8269

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View Online at https://aerobasegroup.com/nsn/5961-01-627-8269 **Inclosure Material:** Plastic **Overall Length:** Between 54.86 millimeters and 56.01 millimeters **Terminal Length:** 25.4 millimeters **Overall Height:** 2.00 millimeters **Overall Width:** 0.71 millimeters **Overall Diameter:** Between 2.00 millimeters and 2.72 millimeters **Function For Which Designed:** Rectifier Joint Electronic Device Engineering Council/jedec/case Outline Designation: **Electrode Internally-electrically Connected To Case:** Collector **Mounting Method: Terminal Features Provided:** Hermetically sealed case and electrostatic sensitive **Semiconductor Material:** Silicon carbide Voltage Rating In Volts Per Characteristic: 60.0 nonrepetitive peak reverse voltage and 60.0 repetitive peak reverse voltage and 42.0 reverse voltage, total rms **Current Rating Per Characteristic:** 5.0 amperes peak forward surge current and 0.7 amperes average forward current averaged over a full 60-hz cycle **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius junction **Product Name:** 1.0a schottky barrier rectifier **Special Features:** Refer to website for additional details **Terminal Type And Quantity:** 2 insulated wire lead Shelf Life: N/a **Unit Of Measure:** 

No

**Demilitarization:** 

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